**IN THE CLAIMS:**

1.-34. (Cancelled)

35. (Currently Amended) A semiconductor light emitting device comprising:

a base substrate (4) made of a highly heat-conductive material; and

a pair of power supply terminal thin-film layers (36, 38), each being provided on different areas of a first main surface of the base substrate, and the pair of power supply terminal thin-film layers being electrically connected to each other via through-holes (42, 46) provided in the base substrate, wherein

a second main surface of the base substrate has provided thereon a semiconductor multilayer epitaxial structure including a first conductive layer (16), a light emitting layer (14), and a second conductive layer (12) formed in the stated order,

the multilayer epitaxial structure is mounted on the base substrate in such a manner that a last epitaxially-grown layer having a structure characteristic of being grown on a single-crystal substrate different from the base substrate is positioned closer to the base substrate than a portion of a first epitaxially-grown layer,

a first electrode thin-film layer (22) is in contact with the first conductive layer,

a second electrode thin-film layer (24) is in contact with the second conductive layer,

a phosphor film covers the semiconductor multilayer epitaxial structure, and

a first thin-film layer (40) and a second thin-film layer (30) electrically connect the first electrode thin-film layer (22) and the second electrode thin-film layer (24) respectively via the through-holes.

36. (Previously Presented) The semiconductor light emitting device of Claim 35, wherein

the multilayer epitaxial structure is formed on the base substrate leaving a space along each edge of a main surface of the base substrate which faces the multilayer epitaxial structure; and

the first through hole and the second through hole are provided in a peripheral portion of the base substrate, the peripheral portion corresponding to the space.

37. (Previously Presented) The semiconductor light emitting device of Claim 35, further comprising:

a metal reflective film that is sandwiched between the multilayer epitaxial structure and the base substrate.

38.-39. (Cancelled)

40. (Previously Presented) The semiconductor light emitting device of Claim 35 wherein

the multilayer epitaxial structure having a structural characteristic of epitaxial growth on a single-crystal substrate different from the base substrate, is mounted on the base substrate.

41.-45. (Cancelled)

46. (Previously Presented) The semiconductor light emitting device of Claim 35, wherein

the first and the second through holes are positioned in a periphery of the base substrate, and

the multilayer epitaxial structure is not positioned on or over the first and second through holes.

47.-51. (Cancelled)

52. (Previously Presented) The semiconductor light emitting device of Claim 35, wherein

the phosphor layer covers an entirety of the base substrate, including surrounding edge portions of the base substrate, and

a peripheral lateral surface of the base substrate and a peripheral lateral surface of the phosphor layer are a continuous surface.

53. (New) The semiconductor light emitting device of Claim 35, wherein

the base substrate is made of one of SiC, AlN, GaN, BN, Si, and sapphire.

54. (New) The semiconductor light emitting device of Claim 35, wherein

the base substrate is made of a highly-resistive semiconductor material.